ERRATA

Erratum: ''Early nitriding stage of evaporated-Ti thin films by N-ion implantation'' [J. Vac. Sci. Technol. A 15, 1848 (1997)]

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[S0734-2101(98)04401-7]

In the author list of the original article Y. Fujino's name was inadvertently spelled incorrectly.

Erratum: ''Low-temperature (<450 °C), plasma-assisted deposition of poly-Si thin films on SiO_2 and glass through interface engineering'' [J. Vac. Sci. Technol. A 15, 1035 (1997)]

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[S0734-2101(98)04501-1]

A sincere apology goes out to Dr. Scott Habermehl of Sandia National Labs for inadvertently excluding references to the original work that he performed on low-temperature homoepitaxial Si film growth using remote-plasma enhanced chemical vapor deposition. Also, acknowledgment is due for his many helpful discussions which lead to the above article. On p. 1036, Table I, both of the ''Stage 2: epi-Si bulk film deposition conditions'' are processes that he optimized while conducting dissertation research at North Carolina State University. Details on these processes may be found in Refs.

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